

Standard Rectifier Module

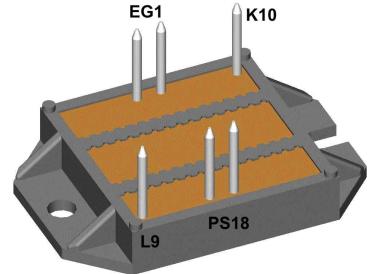
1~
Rectifier

V_{RRM}	=	1600 V
I_{DAV}	=	90 A
I_{FSM}	=	1000 A

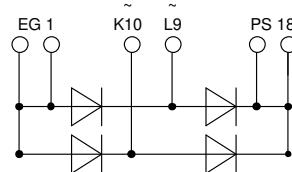
1~ Rectifier Bridge

Part number

VBO88-16NO7



 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For one phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: ECO-PAC2

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 9 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

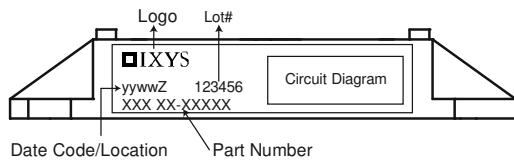
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Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1700	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1600	V
I_R	reverse current	$V_R = 1600 \text{ V}$ $V_R = 1600 \text{ V}$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		100 2	μA mA
V_F	forward voltage drop	$I_F = 50 \text{ A}$	$T_{VJ} = 25^\circ C$		1.13	V
		$I_F = 100 \text{ A}$			1.31	V
		$I_F = 50 \text{ A}$	$T_{VJ} = 125^\circ C$		1.05	V
		$I_F = 100 \text{ A}$			1.28	V
I_{DAV}	bridge output current	$T_C = 115^\circ C$ rectangular	$T_{VJ} = 150^\circ C$ $d = 0.5$		90	A
V_{F0} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ C$		0.80 4.6	V $m\Omega$
R_{thJC}	thermal resistance junction to case				0.6	K/W
R_{thCH}	thermal resistance case to heatsink			0.3		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		205	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		1.00	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 \text{ V}$		1.08	kA
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 150^\circ C$		850	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 \text{ V}$		920	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		5.00	kA^2s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 \text{ V}$		4.85	kA^2s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 150^\circ C$		3.62	kA^2s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 \text{ V}$		3.52	kA^2s
C_J	junction capacitance	$V_R = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	35		pF

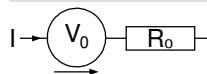
Package ECO-PAC2

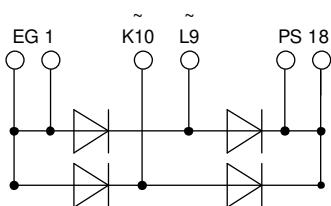
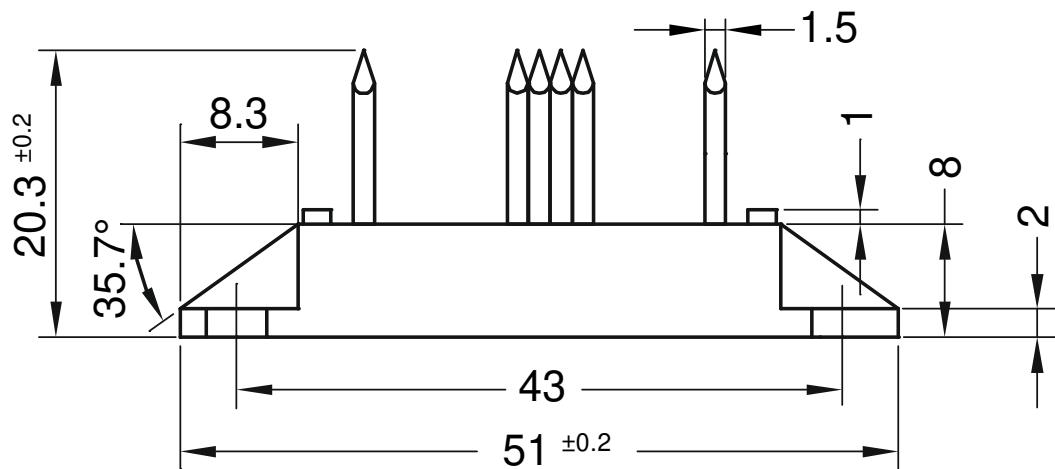
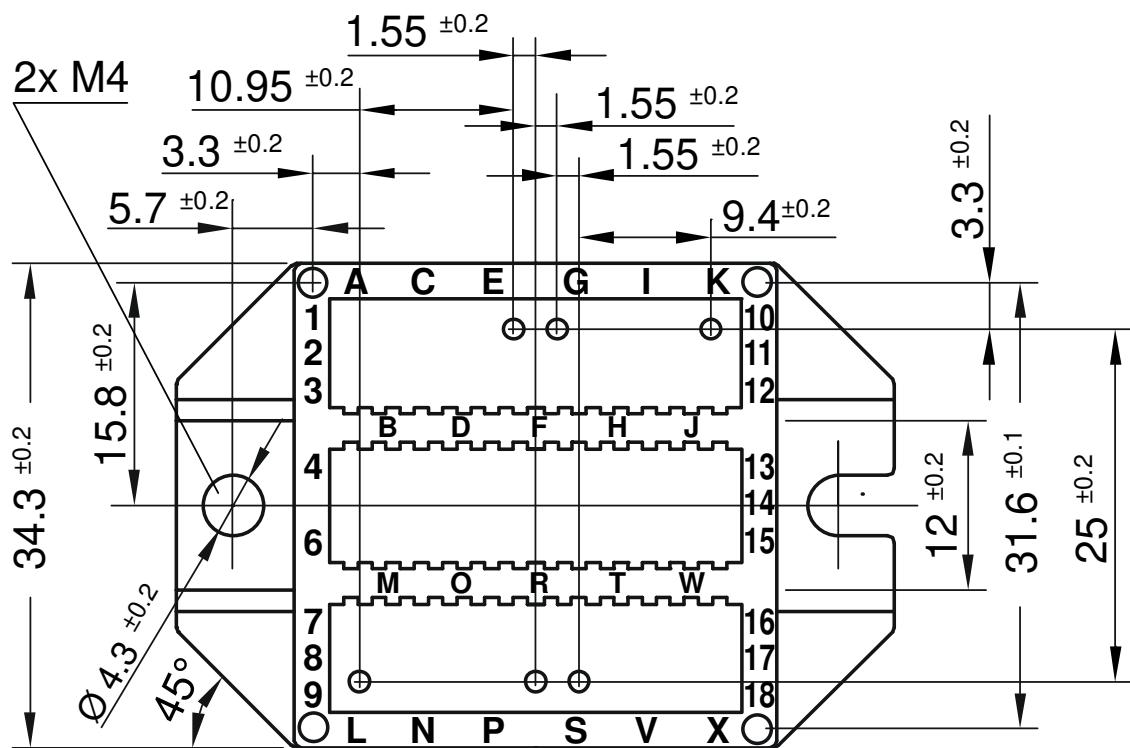
Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				24		g
M_D	mounting torque		1.4		2	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	10.0			mm
V_{ISOL}	isolation voltage	$t = 1 \text{ second}$ $t = 1 \text{ minute}$ 50/60 Hz, RMS; $I_{ISOL} \leq 1 \text{ mA}$	3000 2500			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VBO88-16NO7	VBO88-16NO7	Box	25	494402

Equivalent Circuits for Simulation
^{*}on die level

 $T_{VJ} = 150^\circ\text{C}$

Rectifier
 V_0 *threshold voltage* 0.8 V
 $R_{0\ max}$ *slope resistance ** 3.4 mΩ

Outlines ECO-PAC2


Rectifier

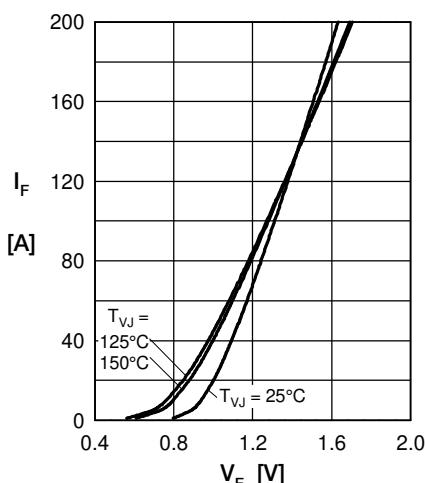


Fig. 1 Forward current vs.
voltage drop per diode

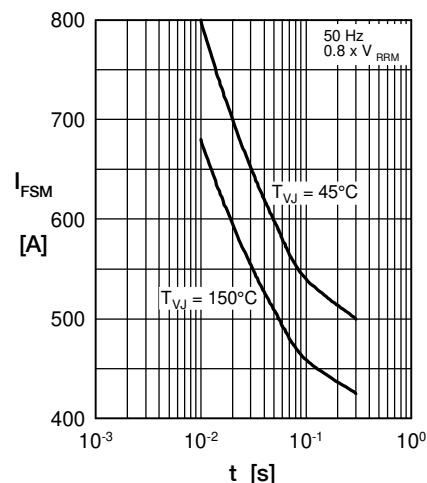


Fig. 2 Surge overload current
vs. time per diode

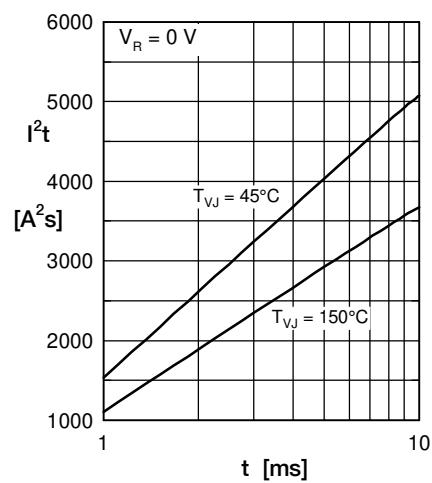


Fig. 3 I^2t vs. time per diode

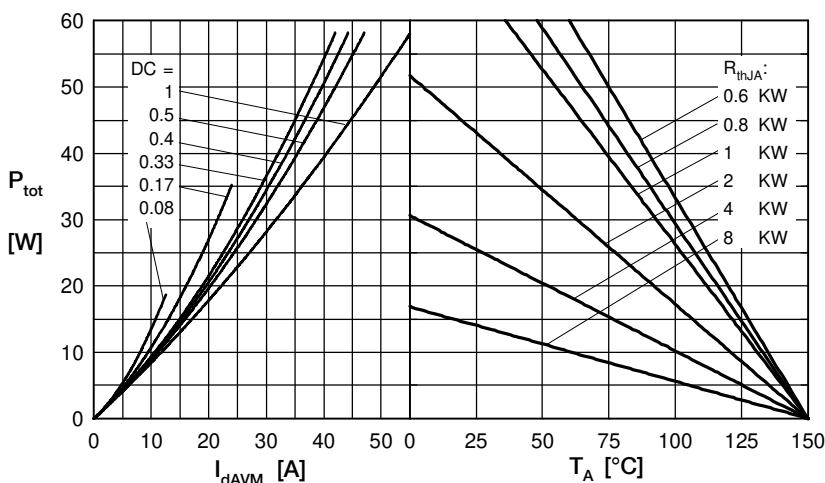


Fig. 4 Power dissipation vs. forward current
and ambient temperature per diode

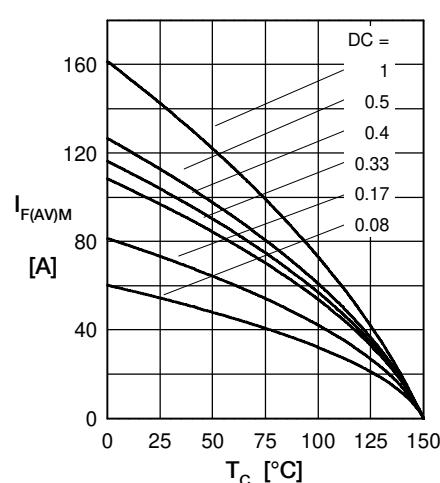


Fig. 5 Max. forward current vs.
case temperature per diode

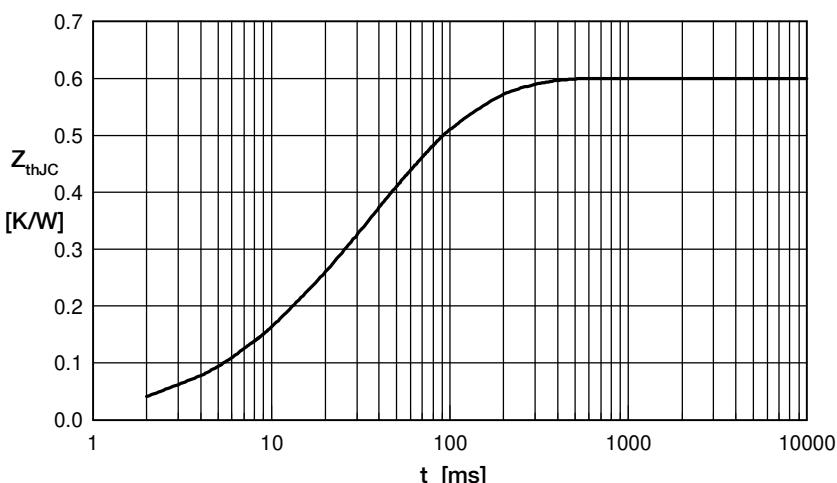


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.08	0.012
2	0.04	0.007
3	0.29	0.036
4	0.19	0.102

